PROCESS FOR TREATING ONO DIELECTRIC FILM OF A FLOATING GATE MEMORY CELL 19/927134

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5 <u>ABSTRACT</u>

A process to deposit a silicon dioxide layer on a silicon nitride layer for an ONO stack of a floating gate transistor. Silicon dioxide is deposited on a silicon nitride layer and annealed in a batch furnace or a single wafer rapid thermal anneal tool in a nitrogen oxide (NO) or nitrous oxide (N $_2$ O) ambient environment.